

**IN THE SPECIFICATION:**

Please replace the title of the application with the following title (the marked-up version appears in the attached appendix):

*A1* -- DYNAMIC SEMICONDUCTOR MEMORY DEVICE HAVING A TRENCH  
CAPACITOR AND METHOD OF MANUFACTURING THE SAME --

Please replace the first paragraph beginning at line 6 and ending with line 9 with the following rewritten paragraph (the marked-up version appears in the attached appendix):

*A2* -- This is a Continuation-In-Part application of U.S. Patent Application Serial No. 08/982,478, filed December 2, 1997, now U.S. Patent No. 6,236,079, the entire contents of which are incorporated herein by reference. --

**IN THE CLAIMS:**

✓ Please cancel claims 1 and 13-17 without prejudice or disclaimer.

Please amend claims 6-10 and 12 as follows (a marked-up version of the claims appears in the attached appendix):

*sub C1*  
*A2* -- 6. (Amended) The semiconductor memory device according to claim 2, wherein said contact layer is buried such that said contact layer extends through the other of said source/drain diffusion layers to reach said capacitor node layer.

7. (Amended) The semiconductor memory device according to claim 2, wherein:

said semiconductor layer comprises a first epitaxially grown layer and a second epitaxially grown layer formed on said first epitaxially grown layer;